

长春新产业光电技术有限公司

Changchun New Industries Optoelectronics Tech. Co., Ltd.

DATA SHEET

MDL-III-852 /1~120mW

INFRARED DIODE LASER AT 852nm

Infrared diode laser at 852nm is made features of round spot, long lifetime, low cost and easy operating, which is widely used in measurement, spectrum analysis, etc.



Wavelength (nm)	852 ± 5	852±5		
Output power (mW)	>1, 5, 10,, 120	>1, 5, 10,, 120		
Spectral line width (nm)	<0.5	<0.5		
Transverse mode	Near TEM ₀₀	Near TEM ₀₀		
Operating mode	CW	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%	<1%, <3%, <5%		
Warm-up time (minutes)	<5	4		
Beam divergence, full angle (mrad)	<1.0	<1.0		
Dimensions of beam at the aperture (mm)	~3.0	~3.0		
Beam height from base plate (mm)	24.8	24.8		
Operating temperature (°C)	10~35	10~35		
Power supply (90-264VAC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM	EWJOARS IV LASER PRODUCT
Modulation option	TTL/Analog 1Hz-51	TTL/Analog 1Hz-5KHz, 1Hz-10KHz, 1Hz-30KHz, and TTL on/off		
Expected lifetime (hours)	10000	10000		
Warranty	1 year	1 year		

MxL-III-852	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
140. 8(L)×73(W) ×46. 2(H) mm ³ , 0.6kg	154 (L) ×155(W) ×95 (H) mm ³ , 1.5kg	DP55L DRIVER	100 (L) ×60(W) ×56 (H) mm ³ , 0.2kg
140. 0(L)×/3(W)×40. 2(II) IIIII , 0.0Kg	1.34 (L) ×1.35(W) ×35 (H) IIIII , 1.3Kg	155 (L) ×150(W) ×05 (H) IIIII , 1.2Kg	100 (L) ×00(W) ×30 (H) IIIII , 0.2Kg

SPECIFICATIONS